

A rectangular block with diagonal hatching, labeled 1.

This cross-sectional view shows a semiconductor device assembly. A top substrate 27 is positioned above a central layer 1. Layer 1 contains a central region 21 and side regions 75. Below layer 1 is a layer 26, which is connected to a central pad 25. The pad 25 is surrounded by a ring 29. Below the ring 29 is a layer 22, which is connected to a central pad 23. The pad 23 is surrounded by a ring 28. A layer 24 is positioned between the ring 28 and the central pad 23. A layer 36 is positioned between the ring 29 and the central pad 25. A layer 30 is positioned between the central pad 25 and the central pad 23. A layer 28 is positioned between the central pad 23 and the central pad 25.

[illegible]

FIG. 1D

FIG. 1D is a cross-sectional view of a device 50. The device 50 includes a substrate 24 and a layer 22 on top of the substrate 24. A structure 26 is formed on the layer 22. The structure 26 includes a central core 21, a surrounding layer 25, and a top layer 23. A cross-section Y1 is shown on the left, and a cross-section Y2 is shown on the right. The cross-section Y2 shows a detailed view of the core 21, layer 25, and a top layer 23, with a central core 21, a surrounding layer 25, and a top layer 23. The cross-section Y2 also shows a central core 21, a surrounding layer 25, and a top layer 23, with a central core 21, a surrounding layer 25, and a top layer 23.

FIG. 2A

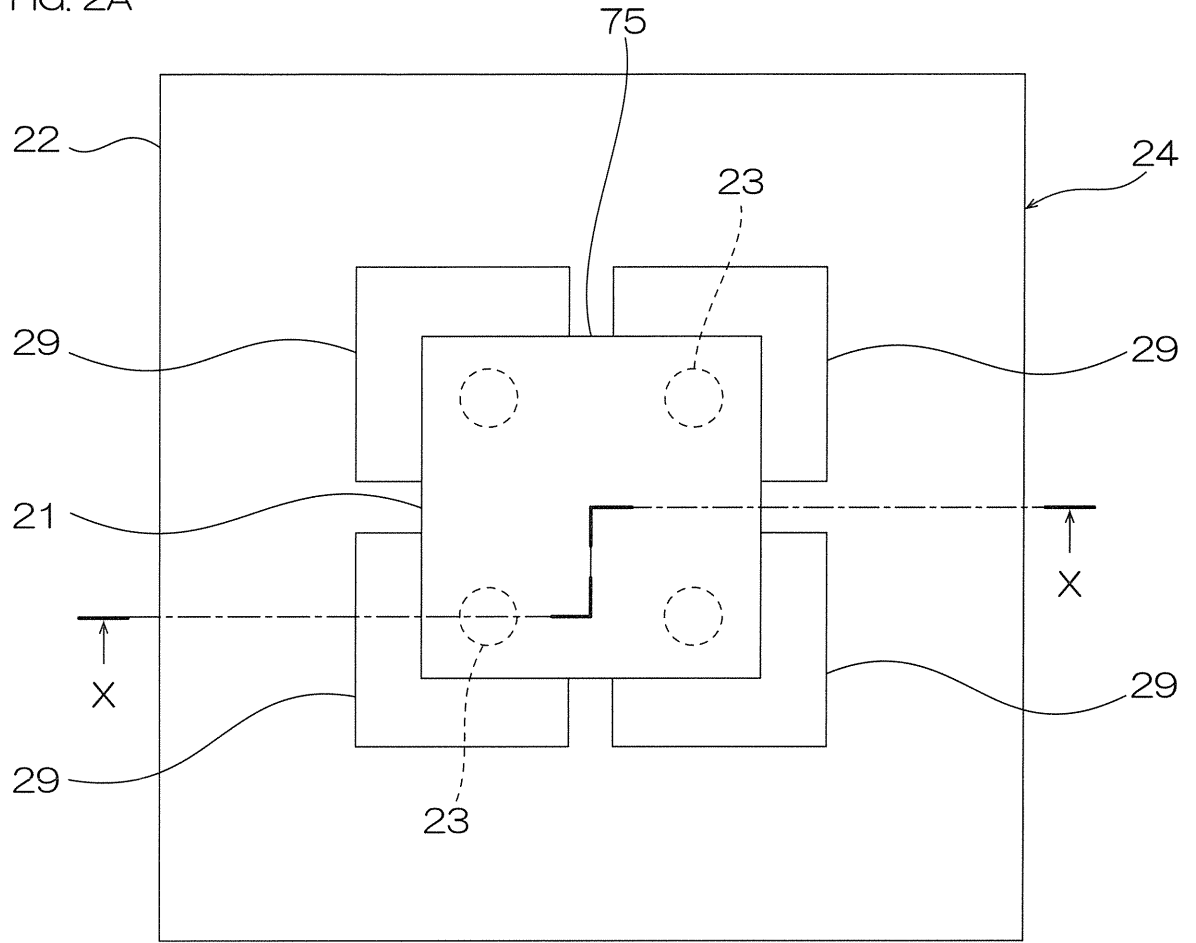


FIG. 2B

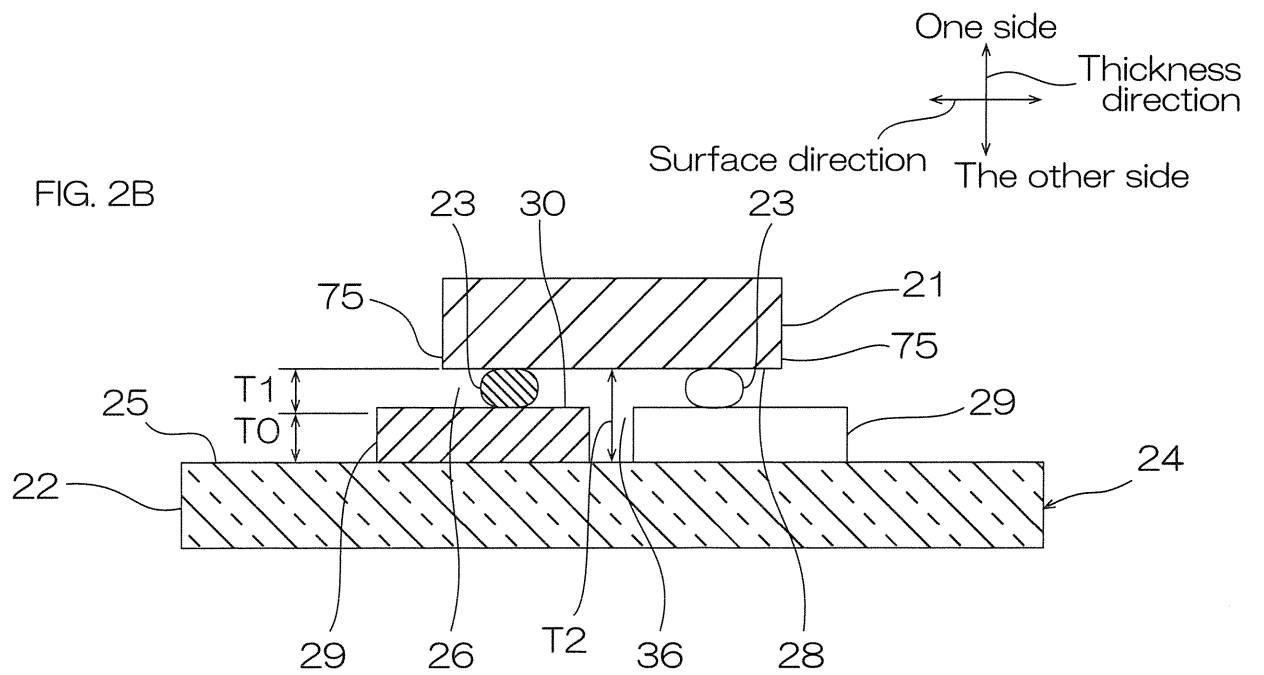


FIG. 3A

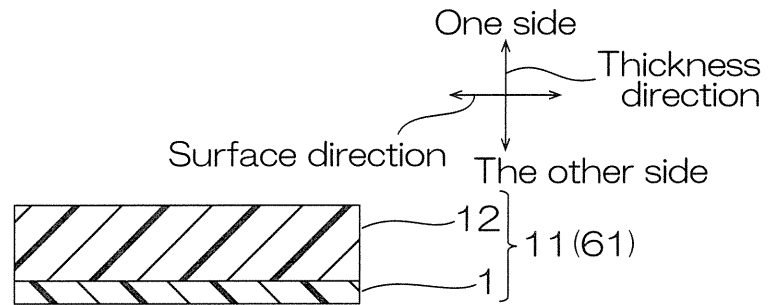


FIG. 3B

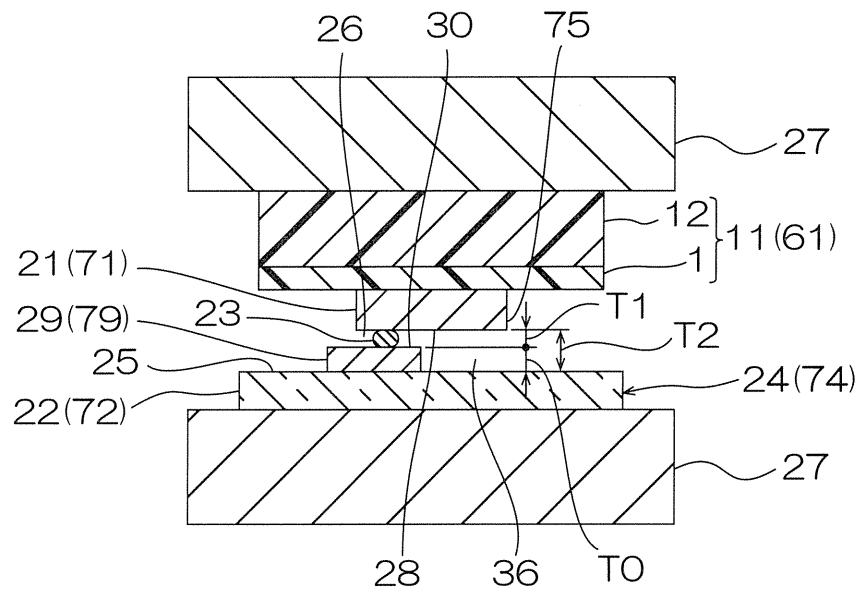


FIG. 3C

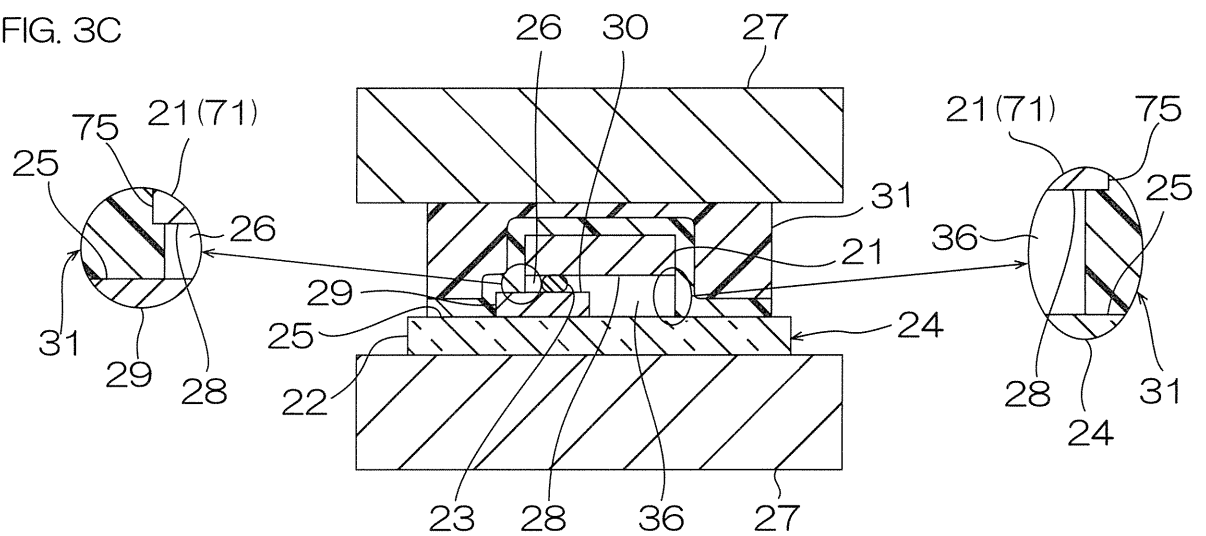


FIG. 3D

